



Halogens free devices

# CHENMKO ENTERPRISE CO.,LTD

## SURFACE MOUNT

### N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 400 Volts CURRENT 10 Ampere

**CHM740ANGP**

**APPLICATION**

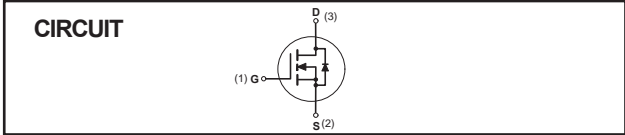
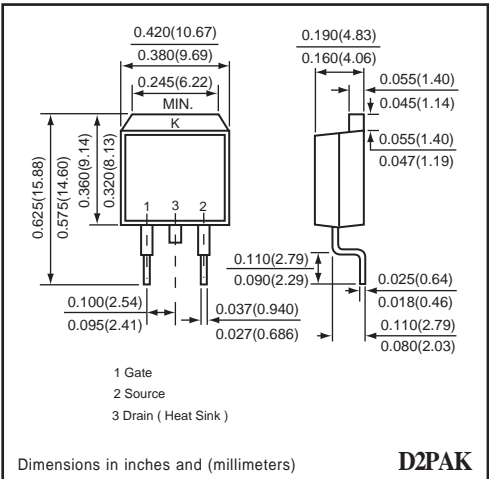
- \* Servo motor control.
- \* Power MOSFET gate drivers.
- \* Other switching applications.

**FEATURE**

- \* Small flat package. (D2PAK)
- \* High density cell design for extremely low  $R_{DS(ON)}$ .
- \* Rugged and reliable.

**CONSTRUCTION**

- \* N-Channel Enhancement



**Absolute Maximum Ratings**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	CHM740ANGP	Units
$V_{DSS}$	Drain-Source Voltage	400	V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Maximum Drain Current - Continuous	10	A
	- Pulsed (Note 3)	40	
$P_D$	Maximum Power Dissipation	125	W
$T_J$	Operating Temperature Range	-55 to 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$

- Note : 1. Surface Mounted on FR4 Board ,  $t \leq 10\text{sec}$   
 2. Pulse Test , Pulse width  $\leq 300\mu\text{s}$  , Duty Cycle  $\leq 2\%$   
 3. Repetitive Rating , Pulse width limited by maximum junction temperature  
 4. Guaranteed by design , not subject to production trsting

**Thermal characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	62.5	$^\circ\text{C/W}$
-----------------	--	------	--------------------

## ELECTRICAL CHARACTERISTIC ( CHM740ANGP )

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
--------	-----------	------------	-----	-----	-----	-------

### OFF CHARACTERISTICS

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	400			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$			50	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
$I_{GSSR}$	Gate-Body Leakage	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

### ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2		4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=6\text{A}$			650	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=50\text{V}, I_D = 6\text{A}$	3	5.4		S

### SWITCHING CHARACTERISTICS (Note 4)

$Q_g$	Total Gate Charge	$V_{DS}=320\text{V}, I_D=10\text{A}$ $V_{GS}=10\text{V}$		52	65	nC
$Q_{gs}$	Gate-Source Charge			6.5		
$Q_{gd}$	Gate-Drain Charge			27		
$t_{on}$	Turn-On Time	$V_{DD}= 200\text{V}$ $I_D = 10\text{A}, V_{GS} = 10\text{ V}$ $R_{GEN}= 9.1\Omega$		16	75	nS
$t_r$	Rise Time			25	125	
$t_{off}$	Turn-Off Time			80	100	
$t_f$	Fall Time			35	60	

### DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

$I_S$	Drain-Source Diode Forward Current	(Note 1)			10	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$I_S = 10\text{A}, V_{GS} = 0\text{ V}$ (Note 2)			2	V